

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	2SK3050TL
Manufacturer:	Rohm Semiconductor
Package:	Please confirm with sales
Availability:	Please confirm with sales

Product Page:

<https://antrexco.com/product/details/rohm-semiconductor/2sk3050tl.html>

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Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

1. TYPE 2SK3050

2. STRUCTURE SILICON N-CHANNEL MOS FIELD EFFECT TRANSISTOR

3. APPLICATIONS SWITCHING

4. ABSOLUTE MAXIMUM RATINGS [Ta=25 °C]

DRAIN-SOURCE VOLTAGE	VDSS	• • •	600V
GATE-SOURCE VOLTAGE	IGSS	• • •	± 30V
DRAIN CURRENT CONTINUOUS	ID	• • •	2A
PULSED	IDP	• • •	6A
	PW	10 μs	DUTY CYCLE 1%
SOURCE CURRENT CONTINUOUS	IS	• • •	2A
PULSED	SP	• • •	6A
	PW	10 μs	DUTY CYCLE 1%
TOTAL POWER DISSIPATION (Tc=25 °C)	PD	• • •	20W
CANNEL TEMPERATURE	Tch	• • •	150
RANGE OF STRAGE TEMPERATURE	Tstg	• • •	-55 ~ 150

5. THERMAL RESISTANCE

CHANNEL TO CASE	Rth(ch-c)	• • •	6.25 /W
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DESIGN

CHECK

APPROVAL

DATE:14.JAN.2000

SPECIFICATION No. : TSQ03019-108-E00

REV.A

ROHM CO., LTD.

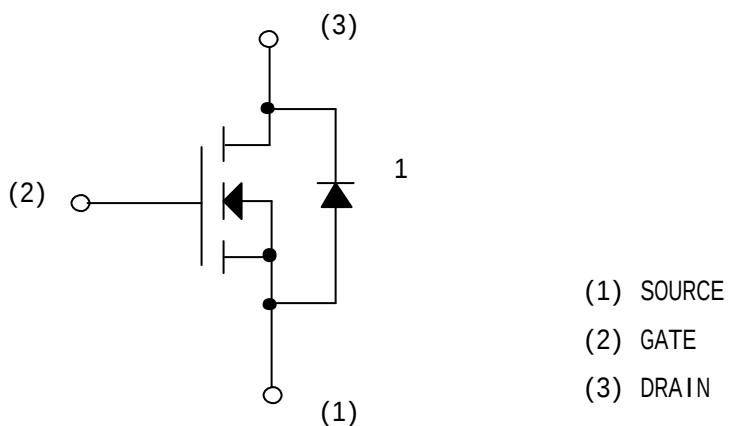
6. ELECTRICAL CHARACTERISTICS [Ta=25]

PARAMETER	ITEM	CONDITION	MIN.	TYP.	MAX.
GATE-SOURCE LEAKAGE	IGSS	VGS= $\pm$ 30V / VDS=0V	-	-	$\pm$ 100nA
DRAIN-SOURCE BREAKDOWN VOLTAGE	V(BR)DSS	ID=1mA / VGS=0V	600V	-	-
ZERO GATE VOLTAGE DRAIN CURRENT	IDSS	VDS=600 / VGS=0V	-	-	100 μ A
GATE THRESHOLD VOLTAGE	VGS(th)	VDS=10V / ID=1mA	2.0V	-	4.0V
STATIC DRAIN-SOURCE ON-STATE RESISTANCE	RDS(on)	ID=1A / VGS=10V	-	4.4 Ω	5.5 Ω
FORWARD TRANSFER ADMITTANCE	Yfs * PULSE	VDS=10V / ID=1A	0.5S	1.0S	-
INPUT CAPACITANCE	Ciss	VDS=10V / VGS=0V f=1MHz	-	280pF	-
OUTPUT CAPACITANCE	Coss		-	48pF	-
REVERSE TRANSFER CAPACITANCE	Crss		-	16pF	-
TURN-ON DELAY TIME	td(on) * PULSE	ID=1A / VDD 300V VGS=10V / RL=300 Ω RGS=10 Ω	-	12ns	-
RISE TIME	tr * PULSE		-	17ns	-
TURN-OFF DELAY TIME	td(off) * PULSE		-	29ns	-
FALL TIME	tf * PULSE		-	105ns	-
TOTAL GATE CHARGE	Qg * PULSE	VDD 300V / VGS=10V ID=2A	-	12.8nC	25.6nC
GATE-SOURCE CHARGE	Qgs * PULSE		-	3.3nC	-
GATE-DRAIN CHARGE	Qgd * PULSE		-	5.5nC	-

7. BODY DIODE CHARACTERISTICS(SOURCE - DRAIN CHARACTERISTICS) [Ta=25]

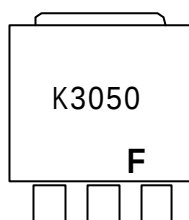
PARAMETER	ITEM	CONDITION	MIN.	TYP.	MAX.
FORWARD VOLTAGE	VSD * PULSE	Is=2A / VGS=0V			2.0 V
REVERSE RECOVERY TIME	Trr * PULSE	IDR=2 / VGS=0V		460nS	
REVERSE RECOVERY CHARGE	Qrr * PULSE	di/dt=100A/uS		2.0uC	

8 . INNER CIRCUIT



1 BODY DIODE

9. MARKING



" K3050 " MEANS 2SK3050 .

" F " MEANS THE PRODUCTION MONTH PLEASE SEE TABLE 1 FOR DETAILS.

Table 1

Production month		1	2	3	4	5	6	7	8	9	10	11	12
Marking	Even year A.D.	A	B	C	D	E	F	G	H	J	K	L	M
	Odd year A.D.	N	P	Q	R	S	T	U	V	W	X	Y	Z